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September 28, 2026
SAIMEMORY Corp.
SHINKO ELECTRIC INDUSTRIES CO., LTD.

SAIMEMORY and SHINKO Sign MOU for the Research and Development, and Commercialization of ZAM, a Next-Generation Memory Technology

SAIMEMORY Corp. (“SAIMEMORY”), a subsidiary of SoftBank Corp., and SHINKO ELECTRIC INDUSTRIES CO., LTD. (“SHINKO”) signed a memorandum of understanding (“MOU”) to establish a partnership for the research and development (“R&D”) and commercialization of Z-Angle Memory (“ZAM”), a next-generation memory technology characterized by high density, high bandwidth and low power consumption.

Under the MOU, SAIMEMORY and SHINKO will build a long-term collaborative relationship spanning the R&D of ZAM, a next-generation memory technology, the establishment of manufacturing technologies and future commercialization, with the goal of bringing this innovative, Japan-originated next-generation memory technology into practical use.

SAIMEMORY is leading the R&D of ZAM under the New Energy and Industrial Technology Development Organization (NEDO)’s “Research and Development Project of the Enhanced Infrastructures for Post-5G Information and Communication Systems / Development of manufacturing technologies for advanced semiconductors (Subsidy, Commission).” * ZAM is an innovative next-generation memory technology designed to achieve high density, high bandwidth, and low power consumption. Through ZAM, a next-generation memory technology, SAIMEMORY aims to enable high capacity and high bandwidth data processing, improve processing performance, and reduce power consumption in data centers and other computing environments used for the training and inference of large-scale AI models.

As an integrated manufacturer of semiconductor packages, SHINKO is building on its longstanding expertise in the design and manufacturing of semiconductor package substrates and high density packaging technologies, and, through its partnership with SAIMEMORY, will work to establish the packaging and manufacturing technologies needed for the R&D and commercialization of ZAM.

Hideya Yamaguchi, President & CEO of SAIMEMORY Corp., said:

“As AI continues to advance, expectations for next-generation memory that combines high performance with low power consumption continue to grow. We are very encouraged to have reached this agreement with SHINKO to build a partnership that extends from R&D through to

future commercialization. By bringing together the technologies and expertise of both companies, we will accelerate the practical implementation of ZAM, an innovative next-generation memory technology originating in Japan, and work to establish memory technology that is competitive in both domestic and global markets.”

Susumu Kurashima, Representative Director of the Board, President and CEO of SHINKO ELECTRIC INDUSTRIES CO., LTD., said:

“With the continued evolution of AI and the further advancement of digitalization, memory technology is one of the critical foundational technologies supporting transformation. We are very pleased to have entered into this MOU with SAIMEMORY, which is advancing the R&D of ZAM, an innovative next-generation memory technology, to build a partnership spanning R&D through to commercialization. By leveraging the combined strengths of SAIMEMORY and SHINKO, and harnessing the technologies and expertise cultivated in Japan over many years, we will strive to advance the practical implementation of next-generation memory and contribute to the development of an advanced digital society powered by AI and other emerging technologies.”

* For details on the NEDO program and the selected project, please visit:

https://www.nedo.go.jp/english/activities/activities_ZZJP_100172.html

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SHINKO ELECTRIC INDUSTRIES CO., LTD.

Public Relations Department, President’s Office

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